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12. (New) An organic film vapor deposition method according to claim 11, wherein the shifted positions of the support elements are configured to prevent film peeling.

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13. (New) An organic film vapor deposition method according to claim 1, wherein the first step comprises supporting multiple substrates, each formed with a scintillator, on at least three protrusions of respective target-support elements disposed on a vapor deposition table so as to keep a distance from said vapor deposition table;

the second step comprises introducing said vapor deposition table having said substrates supported by said respective target-support elements into a vapor deposition chamber of a CVD apparatus; and

the third step comprises depositing, while said table is rotating, an organic film by CVD method onto all surfaces of each substrate provided with a scintillator and introduced into said vapor deposition chamber in a state such that each substrate is supported so as to keep a distance from said vapor deposition table.

14. (New) A method of making a scintillator panel comprising the steps of:  
forming a scintillator on a substrate; and  
forming an organic film according to claim 1.

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**REMARKS**

Applicants have amended claim 1 and added new claims 8-14. Claims 5-7 have been cancelled in a previous amendment. Claims 1-4 and 8-14 are now pending.

The Examiner has rejected claims 1-3 under 35 U.S.C. § 103(a) as being unpatentable over Japanese Publication No. 63-216000 ("JP '000") in view of Japanese Application S61-124574. ("JP '574"). anticipated by JP 8-273622 ("JP '622"); and rejected claim 4 under 35 U.S.C. § 103(a) as unpatentable over these references in view of Laugier (U.S. Patent No. 6,429,437); and rejected claims 1-4 under 35 U.S.C. § 103(a) by being unpatentable over WO 00/63722 in view of JP '574; Applicants traverse these rejections, at least for the following reasons:

Applicants traverse the various art rejections applied to the claims. For example, Applicants submit that the applied references do not disclose or suggest any of Applicants' claimed combinations comprising a rotatable vapor deposition table support for such subject matter can be found in the present specification, with a description of a rotatable vapor deposition table being provided in connection with the text pertaining to Fig. 2 and particularly turntable 30.

Accordingly, Applicants submit that the pending claims patentably distinguish over the applied references of record, at least for the foregoing reasons.

### **CONCLUSION**

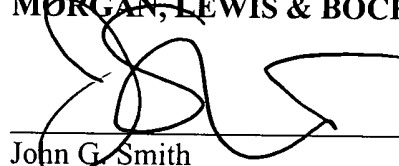
In view of the foregoing, Applicants submit that the pending claims are in condition for allowance, and respectfully request reconsideration and the timely allowance of the pending claims. Should the Examiner feel that there are any issues outstanding after consideration of this response, the Examiner is invited to contact Applicants' undersigned representative to expedite prosecution. A favorable action is awaited.

**Except** for issue fees payable under 37 C.F.R. § 1.18, the Commissioner is hereby authorized by this paper to charge any additional fees during the entire pendency of this application including fees due under 37 C.F.R. § 1.16 and 1.17 which may be required, including any required extension of time fees, or credit any overpayment to Deposit Account No. 50-0310.

This paragraph is intended to be a **CONSTRUCTIVE PETITION FOR EXTENSION OF TIME** in accordance with 37 C.F.R. § 1.136(a)(3).

Respectfully submitted,

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**VERSION WITH THE MARKINGS TO SHOW CHANGES**

**IN THE CLAIMS**

1. **(Once Amended)** An organic film vapor deposition method comprising:  
a first step of supporting a substrate formed with a scintillator on at least three protrusions of a target-support element disposed on a **rotatable** vapor deposition table so as to ~~{keep}~~ **maintain** a distance from said vapor deposition table;  
a second step of introducing said **rotatable** vapor deposition table having said substrate supported by said target-support element into a vapor deposition chamber of a CVD apparatus;  
and  
a third step of depositing an organic film by a CVD method onto **substantially** all **exposed** surfaces of said substrate, provided with said scintillator, introduced into said vapor deposition chamber in a state that said substrate is supported so as to ~~{keep}~~ **maintain** a distance from said **rotatable** vapor deposition table.
8. (New) An organic film vapor deposition method according to claim 1, wherein the rotatable vapor deposition table comprises a turntable.
9. (New) An organic film deposition method according to claim 1, where the third step of depositing the organic film is performed while the vapor deposition table is rotating.

**10. (New) An organic film vapor deposition method according to claim 8, further comprising a fourth step of depositing a second organic film by a CVD method onto substantially all exposed surfaces of the organic film deposited in the third step.**

**11. (New) An organic film vapor deposition method according to claim 10, wherein the fourth step comprises supporting the substrate, after having the organic film deposited in the third step formed thereon, on at least three protrusions of a target-support element disposed on the rotatable vapor deposition table, with the support positions of the protrusions in the fourth step being shifted with respect to the support positions of the protrusions in the first step.**

**12. (New) An organic film vapor deposition method according to claim 11, wherein the shifted positions of the support elements are configured to prevent film peeling.**

**13. (New) An organic film vapor deposition method according to claim 1, wherein the first step comprises supporting multiple substrates, each formed with a scintillator, on at least three protrusions of respective target-support elements disposed on a vapor deposition table so as to keep a distance from said vapor deposition table;**  
**the second step comprises introducing said vapor deposition table having said substrates supported by said respective target-support elements into a vapor deposition chamber of a CVD apparatus; and**

the third step comprises depositing, while said table is rotating, an organic film by CVD method onto all surfaces of each substrate provided with a scintillator and introduced into said vapor deposition chamber in a state such that each substrate is supported so as to keep a distance from said vapor deposition table.

14. (New) A method of making a scintillator panel comprising the steps of:

forming a scintillator on a substrate; and

forming an organic film according to claim 1.